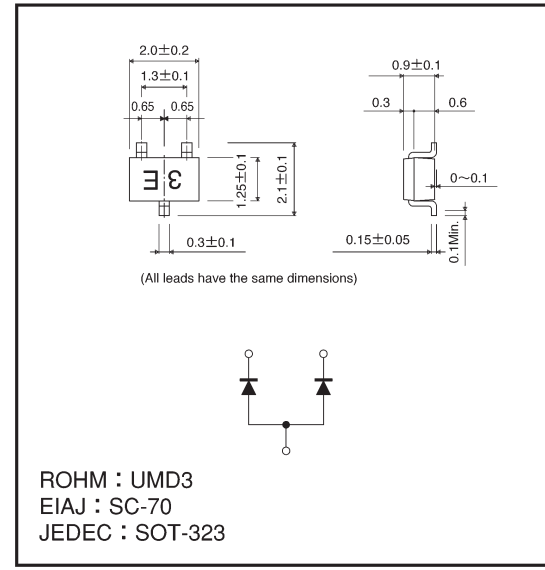
# Schottky barrier diode
## RB717F

●Applications
General purpose detection
High speed switching

●Features
1) Multiple diodes with common anode configuration. (UMD3)
2) High reliability.
3) Low reverse current and low forward voltage.

●Construction
Silicon epitaxial planar

●External dimensions (Units: mm)




●Absolute maximum ratings (Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|---|---|---|---|
| Peak reverse voltage | $V_{RM}$ | 40 | V |
| DC reverse voltage | $V_R$ | 40 | V |
| Mean rectifying current | $I_O$ | 30 | mA |
| Peak forward surge current * | $I_{FSM}$ | 200 | mA |
| Junction temperature | Tj | 125 | ℃ |
| Storage temperature | Tstg | −40～+125 | ℃ |

* 60 Hz for 1 ∽

●Electrical characteristics (Ta = 25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|---|---|---|---|---|---|---|
| Forward voltage | $V_F$ | — | 0.28 | 0.37 | V | $I_F$=1mA |
| Reverse current | $I_R$ | — | 0.05 | 1 | μA | $V_R$=10V |
| Capacitance between terminals | $C_T$ | — | 2.0 | — | pF | $V_R$=1V, f=1MHz |

* ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

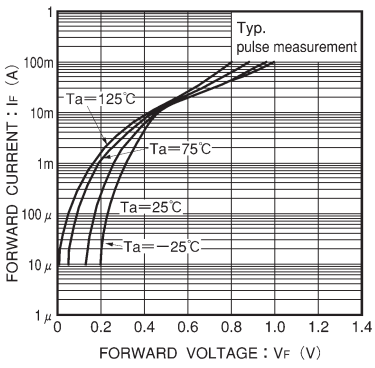



Fig. 1 Forward characteristics

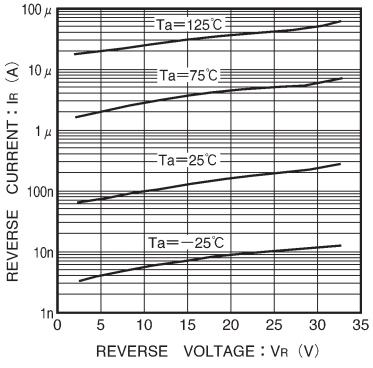



Fig. 2 Reverse characteristics

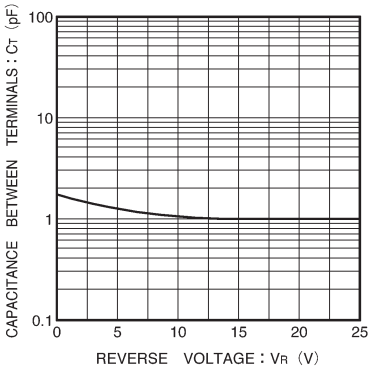



Fig. 3 Capacitance between terminals characteristics

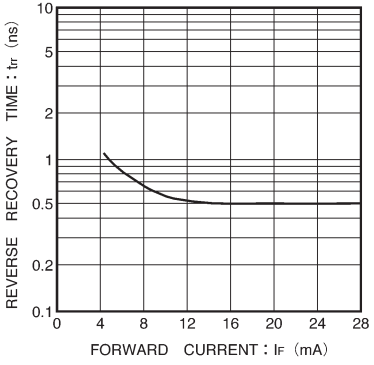



Fig. 4 Reverse recovery time characteristics

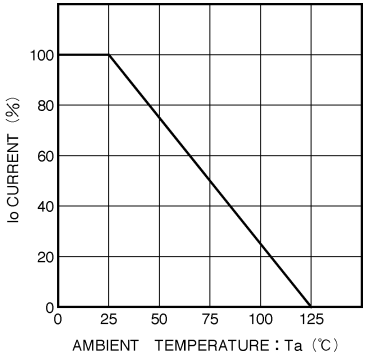



Fig.5 Power Derating (mounting on glass epoxy PCBs)